# $2 \mathrm{~K} \times 8$ Automotive Dual-port Static RAM 

## Features

- True dual-ported memory cells that allow simultaneous reads of the same memory location
- Automotive temperature operation: $-40^{\circ} \mathrm{C}$ to $+115^{\circ} \mathrm{C}$
- $2 \mathrm{~K} x 8$ organization
- High-speed access: 55 ns
- Low operating power: $\mathrm{I}_{\mathrm{Cc}}=120 \mathrm{~mA}$ (max.)
- Fully asynchronous operation
- Automatic power-down
- Master CG5982AF easily expands data bus width to 16 or more bits using slave
- BUSY output flag
- INT flag for port-to-port communication


## Functional Description

The CG5982AF are high-speed CMOS 2K $\times 8$ dual-port static RAMs. Two ports are provided to permit independent access to any location in memory. The CG5982AF can be utilized as either a standalone 8-bit dual-port static RAM or as a MASTER dual-port RAM in conjunction with the CG5982AF SLAVE dual-port device in systems requiring 16-bit or greater word widths. It is the solution to applications requiring shared or buffered data such as cache memory for DSP, bit-slice, or multiprocessor designs.
Each port has independent control pins; chip enable ( $\overline{\mathrm{CE}})$, write enable (R/W), and output enable (OE). BUSY flags are provided on each port. In addition, an interrupt flag (INT) is provided on each port of the 52-pin PLCC version. BUSY signals that the port is trying to access the same location currently being accessed by the other port. On the PLCC version, INT is an interrupt flag indicating that data has been placed in a unique location (7FF for the left port and 7FE for the right port)
An automatic power-down feature is controlled independently on each port by the chip enable (CE) pins.
The CG5982AF is available in a 52-pin PLCC package.

## Logic Block Diagram



## Notes:

1. CG5982AF (Master): BUSY is open-drain output and requires pull-up resistor
2. Open drain outputs; pull-up resistor required.

## Pin Configurations

PLCC
Top View


## Selection Guide

|  | CG5982AF | Unit |
| :--- | :---: | :---: |
| Maximum Access Time | 55 | ns |
| Maximum Operating Current | 120 | mA |
| Maximum Standby Current | 45 | mA |


| Maximum Ratings | DC Input Voltage ......................................-3.5V to +7.0V |  |  |
| :---: | :---: | :---: | :---: |
| (Above which the useful life may be impaired. For user guide- | Output Current into Outputs (LOW)......................... 20 mA |  |  |
| lines, not tested.) | Static Discharge Voltage......................................... > 2001V (per MIL-STD-883, Method 3015) |  |  |
| Storage Temperature ............................. $-65^{\circ} \mathrm{C}$ to $+150^{\circ} \mathrm{C}$ |  |  |  |
| Ambient Temperature with |  |  |  |
| Power Applied...................................... $-55^{\circ} \mathrm{C}$ to $+125^{\circ} \mathrm{C}$ | Operating Range |  |  |
| Supply Voltage to Ground Potential <br> (Pin 48 to Pin 24) ........................................... 0.5 V to +7.0 V | Range | Ambient Temperature | $\mathrm{V}_{\mathrm{cc}}$ |
| DC Voltage Applied to Outputs <br> in High-Z State ............................................... 0.5 V to +7.0 V | Automotive ${ }^{[3]}$ | $-40^{\circ} \mathrm{C}$ to $+115^{\circ} \mathrm{C}$ | $5 \mathrm{~V} \pm 10 \%$ |

Electrical Characteristics Over the Operating Range ${ }^{[4]}$

| Parameter | Description | Test Conditions | CG5982AF |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  | Min. | Max. |  |
| $\mathrm{V}_{\mathrm{OH}}$ | Output HIGH Voltage | $\mathrm{V}_{\mathrm{CC}}=$ Min., $\mathrm{I}_{\mathrm{OH}}=-4.0 \mathrm{~mA}$ | 2.4 |  | V |
| $\mathrm{V}_{\mathrm{OL}}$ | Output LOW Voltage | $\mathrm{I}_{\mathrm{OL}}=4.0 \mathrm{~mA}$ |  | 0.4 | V |
|  |  | $\mathrm{l}_{\mathrm{OL}}=16.0 \mathrm{~mA}^{[5]}$ |  | 0.5 |  |
| $\mathrm{V}_{\mathrm{IH}}$ | Input HIGH Voltage |  | 2.2 |  | V |
| $\mathrm{V}_{\text {IL }}$ | Input LOW Voltage |  |  | 0.8 | V |
| $\mathrm{I}_{\mathrm{IX}}$ | Input Load Current | $\mathrm{GND} \leq \mathrm{V}_{1} \leq \mathrm{V}_{\mathrm{CC}}$ | -5 | +5 | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\mathrm{Oz}}$ | Output Leakage Current | $\mathrm{GND} \leq \mathrm{V}_{\mathrm{O}} \leq \mathrm{V}_{\mathrm{CC}}$, Output Disabled | -5 | +5 | $\mu \mathrm{A}$ |
| los | Output Short-Circuit Current ${ }^{[6]}$ | $\mathrm{V}_{\mathrm{CC}}=$ Max., $\mathrm{V}_{\text {OUT }}=\mathrm{GND}$ |  | -350 | mA |

Note:
3. $\mathrm{T}_{\mathrm{A}}$ is the "instant on" case temperature.
4. See the last page of this specification for Group A subgroup testing information.
5. BUSY and INT pins only.
6. Duration of the short circuit should not exceed 30 seconds.

Electrical Characteristics Over the Operating Range ${ }^{[4]}$ (continued)

| Parameter | Description | Test Conditions |  | CG5982AF |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min. | Max. |  |
| ${ }^{\text {c C }}$ | $\mathrm{V}_{\mathrm{CC}}$ Operating Supply Current | $\overline{C E}=V_{1,7]}$ Outputs Open, $\mathrm{f}=\mathrm{f}_{\mathrm{MAX}}{ }^{[7]}$ | Auto |  | 120 | mA |
| $\mathrm{I}_{\text {SB1 }}$ | Standby Current Both Ports, TTL Inputs | $\begin{aligned} & \overline{\mathrm{CE}}_{\mathrm{L}} \text { and } \overline{\mathrm{CE}}_{\mathrm{R}} \geq \mathrm{V}_{\mathrm{IH}}, \\ & \mathrm{f}=\mathrm{f}_{\mathrm{MAX}}, \end{aligned}$ | Auto |  | 45 | mA |
| ${ }^{\text {SB2 }}$ | Standby Current One Port, TTL Inputs | $\overline{\mathrm{CE}}_{\mathrm{L}}$ or $\overline{\mathrm{CE}}_{\mathrm{R}} \geq \mathrm{V}_{\mathrm{IH}}$, Active Port Outputs Open, $f=f_{\text {MAX }}{ }^{[7]}$ | Auto |  | 90 | mA |
| $\mathrm{I}_{\text {SB3 }}$ | Standby Current Both Ports, CMOS Inputs | Both Ports $\overline{\mathrm{CE}}_{\mathrm{L}}$ and $\overline{\mathrm{CE}}_{\mathrm{R}} \geq$ $\mathrm{V}_{\mathrm{CC}}-0.2 \mathrm{~V}, \mathrm{~V}_{\mathrm{IN}} \geq \mathrm{V}_{\mathrm{CC}}-0.2 \mathrm{~V}$ or $\mathrm{V}_{\text {IN }} \leq 0.2 \mathrm{~V}, \mathrm{f}=0$ | Auto |  | 15 | mA |
| $\mathrm{I}_{\text {SB4 }}$ | Standby Current One Port, CMOS Inputs | One Port $\overline{C E}_{L}$ or $\overline{C E}_{R} \geq V_{C C}$ $-0.2 \mathrm{~V}, \mathrm{~V}_{\text {IN }} \geq \mathrm{V}_{\mathrm{CC}}-0.2 \mathrm{~V}$ or $\mathrm{V}_{\mathrm{IN}} \leq 0.2 \mathrm{~V}$, Active Port Outputs Open, $\mathrm{f}=\mathrm{f}_{\text {MAX }}{ }^{[7]}$ | Auto |  | 85 | mA |

## Capacitance ${ }^{[8]}$

| Parameter | Description | Test Conditions | Max. | Unit |
| :--- | :--- | :--- | :---: | :---: |
| $\mathrm{C}_{\mathrm{IN}}$ | Input Capacitance | $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}, \mathrm{f}=1 \mathrm{MHz}$, | 15 | pF |
| $\mathrm{C}_{\mathrm{OUT}}$ | Output Capacitance | $\mathrm{V}_{\mathrm{CC}}=5.0 \mathrm{~V}$ | 10 | pF |

## AC Test Loads and Waveforms



Switching Characteristics Over the Operating Range ${ }^{[4,9]}$

| Parameter | Description | CG5982AF |  | Unit |
| :---: | :---: | :---: | :---: | :---: |
|  |  | Min. | Max. |  |
| Read Cycle |  |  |  |  |
| $\mathrm{t}_{\mathrm{RC}}$ | Read Cycle Time | 55 |  | ns |
| $\mathrm{t}_{\text {AA }}$ | Address to Data Valid ${ }^{[10]}$ |  | 55 | ns |
| $\mathrm{t}_{\mathrm{OHA}}$ | Data Hold from Address Change | 0 |  | ns |
| $\mathrm{t}_{\text {ACE }}$ | $\overline{\mathrm{CE}}$ LOW to Data Valid ${ }^{[10]}$ |  | 55 | ns |
| $t_{\text {doe }}$ | $\overline{\mathrm{OE}}$ LOW to Data Valid ${ }^{[10]}$ |  | 25 | ns |
| tizoe | $\overline{\mathrm{OE}}$ LOW to Low-Z ${ }^{[8,11]}$ | 3 |  | ns |

7. At $f=f_{\text {MAX }}$, address and data inputs are cycling at the maximum frequency of read cycle of $1 / \mathrm{t}_{\mathrm{rc}}$ and using AC Test Waveforms input levels of GND to 3 V .
8. This parameter is guaranteed but not tested.
9. Test conditions assume signal transition times of 5 ns or less, timing reference levels of 1.5 V , input pulse levels of 0 to 3.0 V , output loading of the specified $\mathrm{IOL}_{\mathrm{OL}} / \mathrm{I}_{\mathrm{OH}}$, and $30-\mathrm{pF}$ load capacitance.
10. AC test conditions use $\mathrm{V}_{\mathrm{OH}}=1.6 \mathrm{~V}$ and $\mathrm{V}_{\mathrm{OL}}=1.4 \mathrm{~V}$.
11. At any given temperature and voltage condition for any given device, $t_{\text {HZCE }}$ is less than $t_{\text {LZCE }}$ and $t_{\text {HZOE }}$ is less than $t_{\text {LZoe }}$.

Switching Characteristics Over the Operating Range ${ }^{[4,9]}$（continued）

| Parameter | Description | CG5982AF |  | Unit |
| :---: | :---: | :---: | :---: | :---: |
|  |  | Min． | Max． |  |
| $\mathrm{t}_{\text {Hzoe }}$ | $\overline{\mathrm{OE}}$ HIGH to High－Z ${ }^{[8,11,12]}$ |  | 25 | ns |
| $\mathrm{t}_{\text {HZCE }}$ | $\overline{\text { CE }}$ HIGH to High－Z ${ }^{[8,11,12]}$ |  | 25 | ns |
| $\mathrm{t}_{\text {PU }}$ | $\overline{\text { CE }}$ LOW to Power－Up ${ }^{[8]}$ | 0 |  | ns |
| $\mathrm{t}_{\text {PD }}$ | $\overline{\mathrm{CE}}$ HIGH to Power－Down ${ }^{[8]}$ |  | 35 | ns |
| Write Cycle ${ }^{[13]}$ |  |  |  |  |
| $\mathrm{t}_{\text {wc }}$ | Write Cycle Time | 55 |  | ns |
| $\mathrm{t}_{\text {SCE }}$ | $\overline{\text { CE }}$ LOW to Write End | 40 |  | ns |
| $\mathrm{t}_{\text {AW }}$ | Address Set－up to Write End | 40 |  | ns |
| $\mathrm{t}_{\mathrm{HA}}$ | Address Hold from Write End | 2 |  | ns |
| $\mathrm{t}_{\text {SA }}$ | Address Set－up to Write Start | 0 |  | ns |
| $\mathrm{t}_{\text {PWE }}$ | R／产 Pulse Width | 30 |  | ns |
| $\mathrm{t}_{\text {SD }}$ | Data Set－up to Write End | 20 |  | ns |
| $\mathrm{t}_{\mathrm{HD}}$ | Data Hold from Write End | 0 |  | ns |
| $\mathrm{t}_{\text {HzWE }}$ | R／产 LOW to High－Z ${ }^{[8]}$ |  | 25 | ns |
| tızWE | R／్̄W HIGH to Low－Z ${ }^{[8]}$ | 0 |  | ns |
| Busy／Interrupt Timing |  |  |  |  |
| $\mathrm{t}_{\text {BLA }}$ | $\overline{\text { BUSY }}$ LOW from Address Match |  | 30 | ns |
| $\mathrm{t}_{\text {BHA }}$ | $\overline{\text { BUSY }}$ HIGH from Address Mismatch ${ }^{[14]}$ |  | 30 | ns |
| $\mathrm{t}_{\text {BLC }}$ | $\overline{\text { BUSY }}$ LOW from $\overline{C E}$ LOW |  | 30 | ns |
| $\mathrm{t}_{\mathrm{BHC}}$ | $\overline{\text { BUSY }}$ HIGH from $\overline{\mathrm{CE}}$ HIGH ${ }^{[14]}$ |  | 30 | ns |
| $\mathrm{t}_{\text {PS }}$ | Port Set－up for Priority | 5 |  | ns |
| $\mathrm{t}_{\text {WB }}$ | R／产 LOW after $\overline{\text { BUSY }}$ LOW | 0 |  | ns |
| $\mathrm{t}_{\text {WH }}$ | R／̄W HIGH after $\overline{\text { BUSY }}$ HIGH | 35 |  | ns |
| $\mathrm{t}_{\text {BDD }}$ | $\overline{\text { BUSY }}$ HIGH to Valid Data |  | 45 | ns |
| $\mathrm{t}_{\text {DDD }}$ | Write Data Valid to Read Data Valid |  | Note 15 | ns |
| $\mathrm{t}_{\text {WDD }}$ | Write Pulse to Data Delay |  | Note 15 | ns |
| Interrupt Timing ${ }^{[15]}$ |  |  |  |  |
| ${ }^{\text {twins }}$ | R／产 to İINTERRUPT Set Time |  | 45 | ns |
| teins | $\overline{\mathrm{CE}}$ to INTERRUPT Set Time |  | 45 | ns |
| tins | Address to INTERRUPT Set Time |  | 45 | ns |
| toinr | $\overline{\mathrm{OE}}$ to INTERRUPT Reset Time ${ }^{[14]}$ |  | 45 | ns |
| $\mathrm{t}_{\text {EINR }}$ | $\overline{\mathrm{CE}}$ to INTERRUPT Reset Time ${ }^{[14]}$ |  | 45 | ns |
| $\mathrm{t}_{\text {INR }}$ | Address to INTERRUPT Reset Time ${ }^{[14]}$ |  | 45 | ns |

Notes：
12．$t_{\text {LZCE }}, t_{\text {LZWE }}, t_{H Z O E}, t_{\text {LZOE }} t_{H Z C E}$ ，and $t_{H Z W E}$ are tested with $C_{L}=5 \mathrm{pF}$ ，as in（b）of $\underline{A C}$ Test Loads．Transition is measured $\pm 500$ mV from steady－state voltage．
13．The internal write time of the memory is defined by the overlap of CE LOW and R／W LOW．Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH．The data input setup and hold timing should be referenced to the rising edge of the signal that terminates the write．
14．These parameters are measured from the input signal changing，until the output pin goes to a high－impedance state．
15．A write operation on Port A，where Port A has priority，leaves the data on Port B＇s outputs undisturbed until one access time after one of the following：
BUSY on Port B goes HIGH．
Port B＇s address toggled．
CE for Port B is toggled．
$R / \bar{W}$ for Port $B$ is toggled during valid read．

## Switching Waveforms

## Read Cycle No. 1 (Either Port-Address Access) ${ }^{[16,17]}$



Read Cycle No. 2 (Either Port- $\overline{\mathrm{CE}} / \overline{\mathrm{OE}})^{[16,18]}$


Read Cycle No. 3 (Read with $\overline{B U S Y}$ Master)


Notes:
16. R/W is HIGH for read cycle.
17. Device is continuously selected, $\overline{C E}=V_{\Perp}$ and $\overline{O E}=V_{I L}$.
18. Address valid prior to or coincident with CE transition LOW

Switching Waveforms (continued)
Write Cycle No. $1\left(\overline{\mathrm{OE}}\right.$ Three-States Data I/Os—Either Port) ${ }^{[13,19]}$


Write Cycle No. 2 (R/W Three-States Data I/Os—Either Port) ${ }^{[13,20]}$


Notes:
19. If $O E$ is LOW during a R/W controlled write cycle, the write pulse width must be the larger of $\mathrm{t}_{\mathrm{PWE}}$ or $\mathrm{t}_{\mathrm{HZWE}}+\mathrm{t}_{\mathrm{SD}}$ to allow the data I/O pins to enter high impedance and for data to be placed on the bus for the required $\mathrm{t}_{\mathrm{SD}}$.
20. If the $\overline{C E}$ LOW transition occurs simultaneously with or after the R/W LOW transition, the outputs remain in a high-impedance state.

Switching Waveforms (continued)
Busy Timing Diagram No. 1 ( $\overline{C E}$ Arbitration)
$\overline{\mathrm{CE}}_{\mathrm{L}}$ Valid First:


Busy Timing Diagram No. 2 (Address Arbitration)


Switching Waveforms (continued)
Busy Timing Diagram No. 3 (Write with BUSY, Slave)


## Interrupt Timing Diagrams ${ }^{\text {[16] }}$

Left Side Sets $\overline{\mathrm{INT}}_{\mathrm{R}}$ :


Right Side Clears $\overline{\mathrm{INT}}_{\mathrm{R}}$ :


Right Side Sets $\overline{\mathrm{INT}}_{\mathrm{L}}$ :


Interrupt Timing Diagrams ${ }^{[16]}$ (continued)
Left Side Clears $\overline{\mathrm{NT}}_{\mathrm{L}}$ :


## Typical DC and AC Characteristics



## Ordering Information

| Speed (ns) | Ordering Code | Package <br> Name | Package Type | Operating <br> Range |
| :---: | :--- | :---: | :--- | :--- |
| 55 | CG5982AF | J69 | 52-lead Plastic Leaded Chip Carrier | Automotive |

## Package Diagrams

## 52-lead Plastic Leaded Chip Carrier J69



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## Document History Page

| Document Title: CG5982AF 2K x 8 Automotive Dual-port Static RAM <br> Document Number: 38-06067 |  |  |  |  |
| :---: | :---: | :---: | :---: | :--- |
| REV. | ECN | Issue <br> Date | Orig. of <br> Change | Description of Change |
| $* *$ | 119657 | $10 / 10 / 02$ | NIM | Customized data sheet to meet special requirements for CG5982AF; <br> automotive temperature $-40^{\circ} \mathrm{C}$ to $+115^{\circ} \mathrm{C}$; base part in CY7C136 |
| *A | 121488 | $12 / 09 / 02$ | OOR | Fixed Typo- changed 5 mA to $5 \mu \mathrm{~A}$ (p.2) |
| *B | 393195 | SEE ECN | KGH | Included the automotive temperature operation range to the Features <br> section <br> Removed the micron CMOS size and the 52-pin PLCC references from the <br> Features section <br> Added Automotive to the title description |
| *C | 421244 | See ECN | ODC | Add to external web. |

